ABSTRACT

The present discloses provides a memory device and a method of operating the memory device. The memory device includes first main plugs formed in a vertical direction over a substrate and arranged in a first direction, second main plugs, third main plugs arranged between the first and second main plugs, the third main plugs adjacent to the first and second main plugs, and bit lines above the first to third main plugs, wherein each of the first to third main plugs includes first and second sub-plugs facing each other, wherein portions of the first and second sub-plugs included in each of the first and third main plugs are coupled to different select lines, and wherein portions of the first and second sub-plugs included in each of the second and third main plugs are coupled to different select lines.

FIG. 9